

3-13-02
PB

Docket: 740819-723

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of
Masahiro ISHIDA
Japanese Priority Application No. 2001-019549
Japanese Priority Date: January 29, 2001
For: METHOD OF MANUFACTURING
NITRIDE SEMICONDUCTOR SUBSTRATE
)
)
) Attn: Applications
) Branch
)
) Date: January 2, 2001

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INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents and Trademarks
Washington, D.C. 20231

Sir:

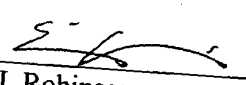
In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

At least some of the references listed on PTO Form-1449 are discussed in the specification of the present application.

Copies of these references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Japanese Patent No. 3091593 was laid open to public inspection under Japanese Patent Laid Open Gazette No. 6-216409, and an English language Abstract of 06-216409 is enclosed.

Respectfully submitted,


Eric J. Robinson
Registration No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110